

Description

Advanced process capability has been used to maximise the performance of this 60V, NPN transistor. The W-DFN2020-3/SWP (Type A) package offers lower profile and the derating up to +175°C allows higher dissipation for applications where power density is of utmost importance.

Features

- $BV_{CEO} > 60V$
- $I_C = 4A$ Continuous Collector Current
- Low Saturation Voltage (100mV Max @1A)
- $R_{SAT} = 60m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified up to 6A for High Current Gain Hold Up
- Tighter Gain Specification
- Low Profile 0.62mm High Package for Thin Applications
- Sidewall Tin Plating for Wettable Flanks in AOI
- $R_{\theta JA}$ Efficient, 60% Lower than SOT23
- 4mm² Footprint, 50% Smaller Than SOT23
- Rated +175°C – Ideal for High Temperature Environment
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DXTN10060DFJBWQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.**

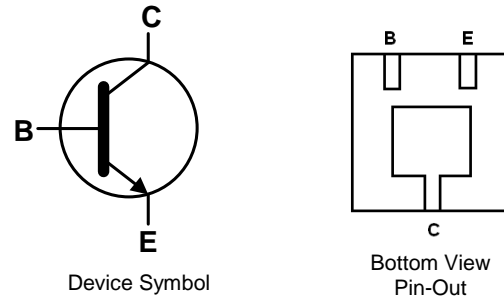
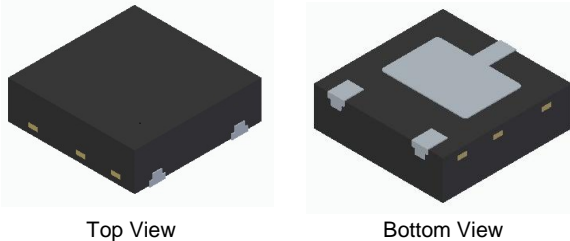
Mechanical Data

- Case: W-DFN2020-3
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin, Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.01 grams (Approximate)

Applications

- Automotive Systems
 - MOSFET Gate Driving
 - DC-DC Converters
 - Motor Control
 - Power Switches

W-DFN2020-3/SWP (Type A)



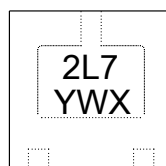
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTN10060DFJBWQ-7	Automotive	2L7	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

W-DFN2020-3/SWP (Type A)



- 2L7 = Product Type Marking Code
- Y = Year: 0~9
- W = Week: A~Z: 1~26 Week; a~z: 27~52 Week; z Represents 52 and 53 Week
- X = A~Z: Internal Code

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	60	
Emitter-Base Voltage	V _{EBO}	8	
Peak Pulse Current	I _{CM}	6	A
Continuous Collector Current	(Note 5)	4	
	(Note 6)	4.3	
Base Current	I _B	1	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

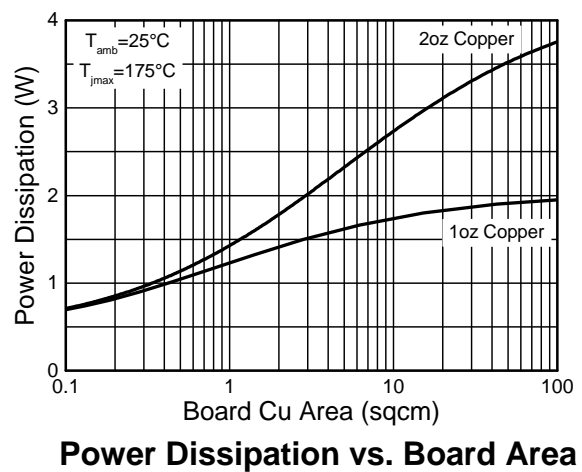
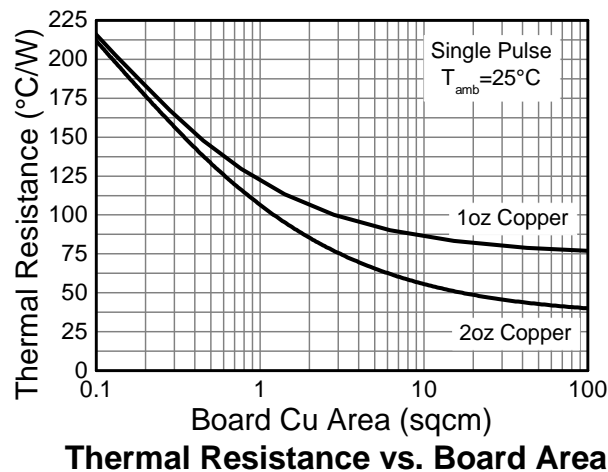
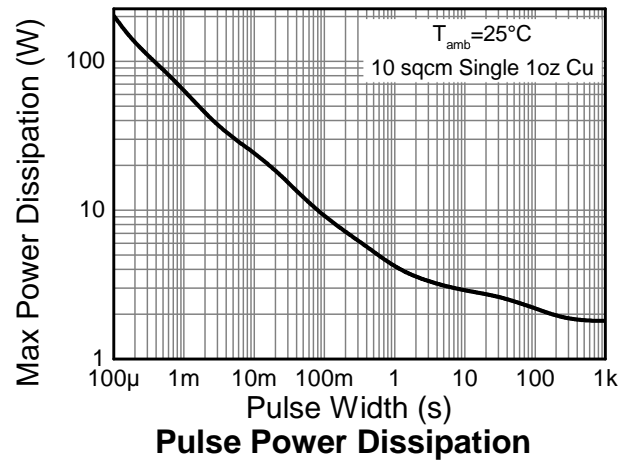
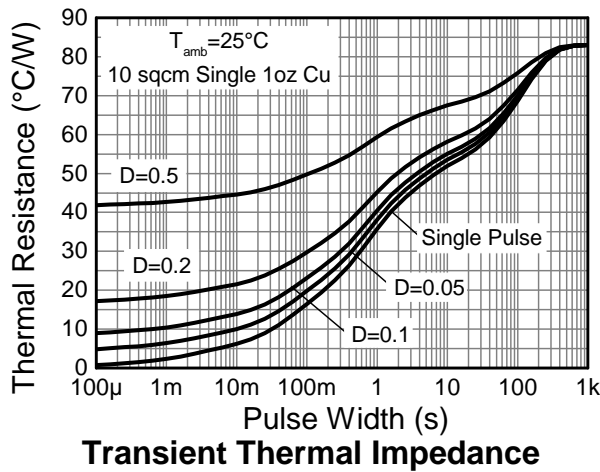
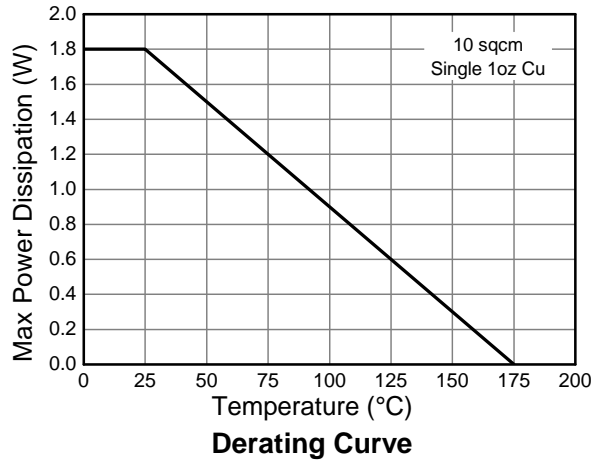
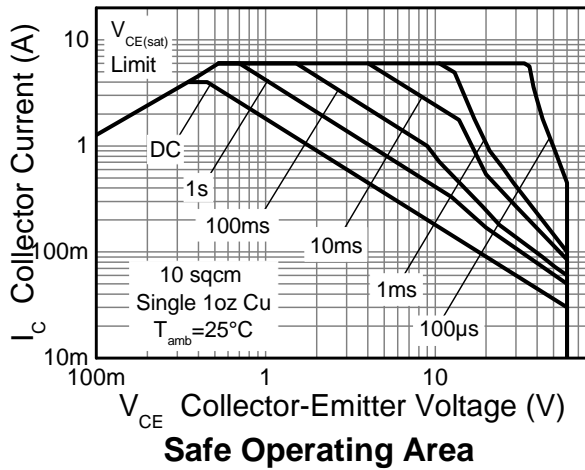
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	1.8	W
		12	
Linear Derating Factor		2.94	mW/°C
		19.6	
Thermal Resistance, Junction to Ambient	R _{θJA}	83	°C/W
		51	
Thermal Resistance, Junction to Lead	R _{θJL}	16.8	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the exposed collector pad on 31mm x 31mm (10cm²) 1oz copper that is on a single sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state. The entire exposed collector pad is attached to the heatsink.
 6. Same as Note 5, except the device is measured at t ≤ 5 sec.
 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

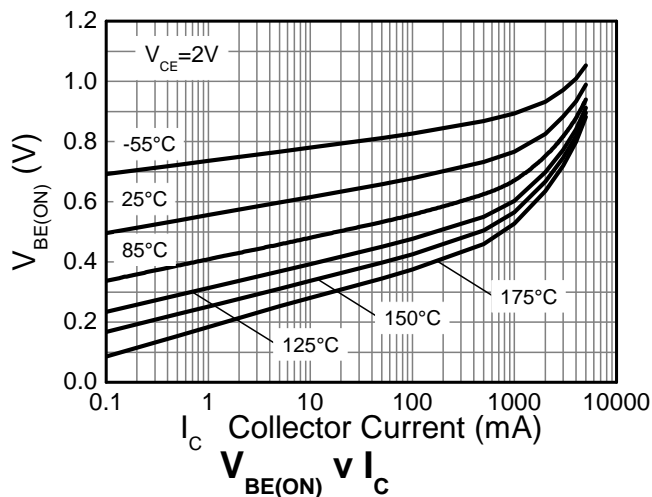
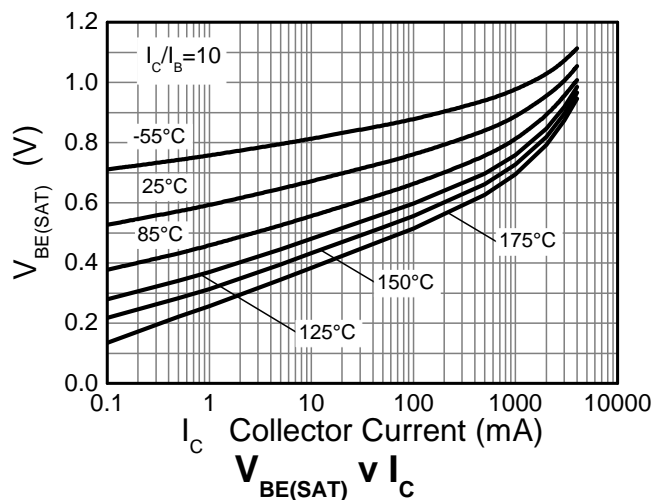
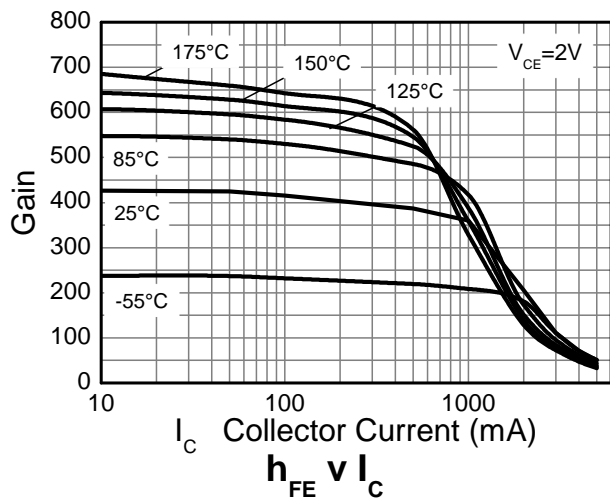
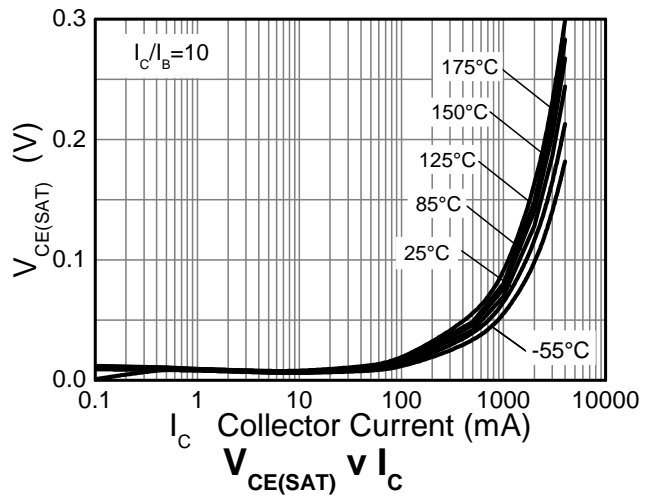
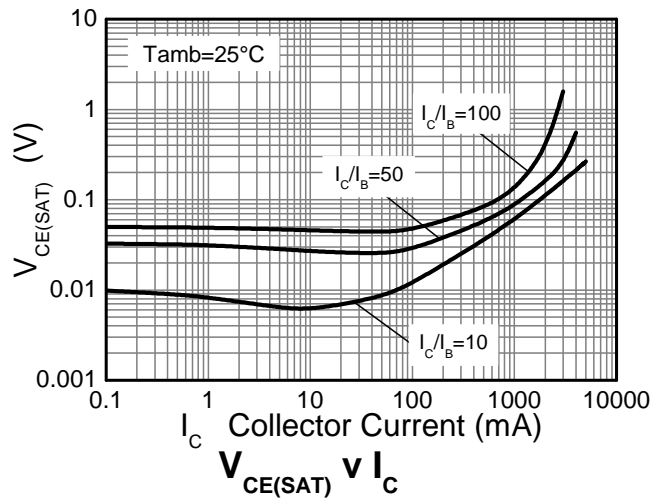


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	187	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	60	66	-	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	8	9	-	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	-	2	100	nA	V _{CB} = 120V
Emitter Cutoff Current	I _{EBO}	-	2	100	nA	V _{EB} = 7V
Collector Emitter Cutoff Current	I _{CES}	-	2	100	nA	V _{CES} = 48V
Static Forward Current Transfer Ratio (Note 9)	h _{FE}	250	444	550	-	I _C = 10mA, V _{CE} = 2V
		340	425	500		I _C = 200mA, V _{CE} = 2V
		250	363	--		I _C = 1A, V _{CE} = 2V
		140	205	--		I _C = 2A, V _{CE} = 2V
		20	40	--		I _C = 6A, V _{CE} = 2V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(SAT)}	--	12	20	mV	I _C = 0.1A, I _B = 10mA
		--	70	100		I _C = 1A, I _B = 50mA
		--	125	160		I _C = 1A, I _B = 10mA
		--	150	200		I _C = 2A, I _B = 50mA
		--	200	300		I _C = 3A, I _B = 100mA
		--	240	320		I _C = 4A, I _B = 200mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	--	0.94	1.00	V	I _C = 4A, V _{CE} = 2V
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	--	1.00	1.07	V	I _C = 4A, I _B = 200mA
Output Capacitance	C _{obo}	--	14	--	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T	125	--	--	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Turn-On Time	t _{ON}	--	200	--	ns	V _{CC} = 10V, I _C = 1A
Turn-Off Time	t _{OFF}	--	700	--	ns	I _{B1} = -I _{B2} = 10mA

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

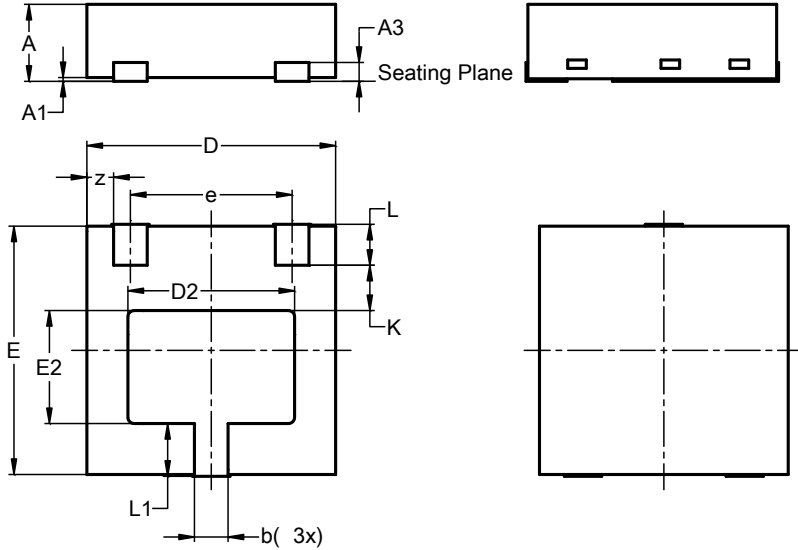
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-DFN2020-3/SWP (Type A)

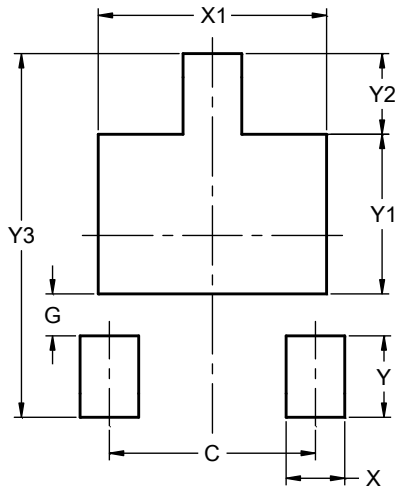


W-DFN2020-3 /SWP (Type A)			
Dim	Min	Max	Typ
A	0.57	0.67	0.62
A1	0.00	0.05	0.03
A3	—	—	0.152
b	0.22	0.32	0.27
D	1.95	2.05	2.00
D2	1.24	1.44	1.34
D4	0.56	0.76	0.66
E	1.95	2.05	2.00
E2	0.81	1.01	0.91
e	—	—	1.30
k	—	—	0.365
L	0.28	0.38	0.33
L1	0.375	0.475	0.425
z	—	—	0.215
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-DFN2020-3/SWP (Type A)



Dimensions	Value (in mm)
C	1.300
G	0.265
X	0.370
X1	1.440
Y	0.515
Y1	1.010
Y2	0.510
Y3	2.300

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